N-channel dual-gate MOS-FET | BF908WR

FEATURES

- High forward transfer admittance
- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz.

APPLICATIONS

- VHF and UHF applications with 12 V supply voltage, such as television tuners and professional communications equipment.

DESCRIPTION

Depletion type field effect transistor in a plastic microminiature SOT343R package. The transistor is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

CAUTION
The device is supplied in an antistatic package. The gate-source input must be protected against static discharge during transport or handling.

PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g_2	gate 2
4	g_1	gate 1

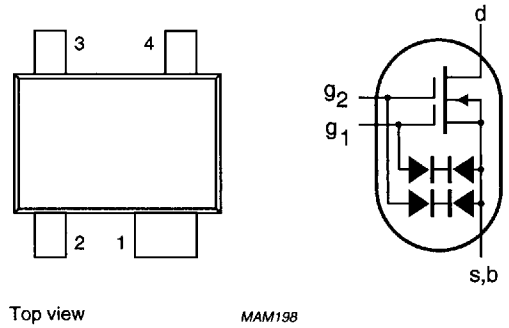

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Fig.1 Simplified outline (SOT343R) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage		–	–	12	V
I_D	drain current		–	–	40	mA
P_{tot}	total power dissipation		–	–	300	mW
T_j	operating junction temperature		–	–	150	°C
$\|y_{fs}\|$	forward transfer admittance		36	43	50	mS
C_{ig1-s}	input capacitance at gate 1		2.4	3.1	4	pF
C_{rs}	reverse transfer capacitance	f = 1 MHz	20	30	45	fF
F	noise figure	f = 800 MHz	–	1.5	2.5	dB

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	12	V
I_D	drain current		–	40	mA
I_{G1}	gate 1 current		–	±10	mA
I_{G2}	gate 2 current		–	±10	mA
P_{tot}	total power dissipation	up to T_{amb} = 45 °C; see Fig.2; note 1	–	300	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	+150	°C

Note

1. Device mounted on a printed-circuit board.

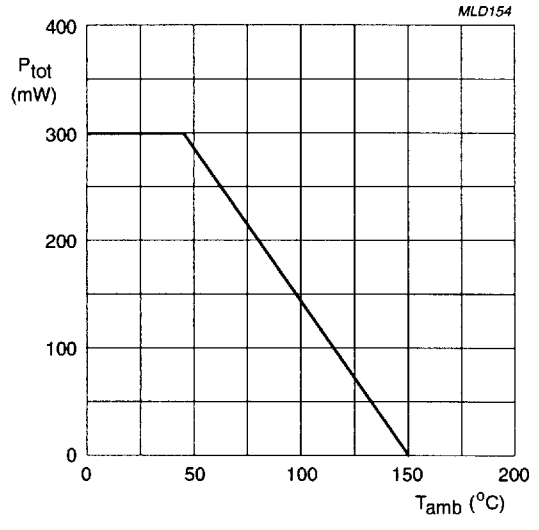


Fig.2 Power derating curve.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	350	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	T_s = 87 °C; note 2	210	K/W

Notes

1. Device mounted on a printed-circuit board.
2. T_s is the temperature at the soldering point of the source lead.

STATIC CHARACTERISTICS

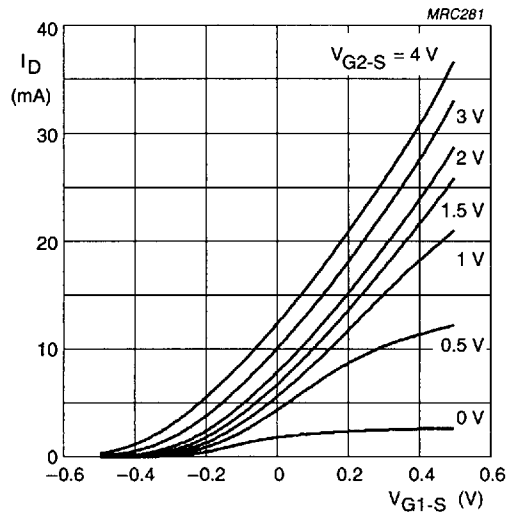
T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)G1\text{-}SS}$	gate 1-source breakdown voltage	$V_{G2\text{-}S} = V_{DS} = 0$; $I_{G1\text{-}S}$ = 10 mA	8	–	20	V
$V_{(BR)G2\text{-}SS}$	gate 2-source breakdown voltage	$V_{G1\text{-}S} = V_{DS} = 0$; $I_{G2\text{-}S}$ = 10 mA	8	–	20	V
$V_{(P)G1\text{-}S}$	gate 1-source cut-off voltage	$V_{G2\text{-}S}$ = 4 V; V_{DS} = 8 V; I_D = 20 µA	–	–	–2	V
$V_{(P)G2\text{-}S}$	gate 2-source cut-off voltage	$V_{G1\text{-}S}$ = 4 V; V_{DS} = 8 V; I_D = 20 µA	–	–	–1.5	V
I_{DSS}	drain-source current	$V_{G2\text{-}S}$ = 4 V; V_{DS} = 8 V; $V_{G1\text{-}S} = 0$	3	15	27	mA
$I_{G1\text{-}SS}$	gate 1 cut-off current	$V_{G2\text{-}S} = V_{DS} = 0$; $V_{G1\text{-}S}$ = 5 V	–	–	50	nA
$I_{G2\text{-}SS}$	gate 2 cut-off current	$V_{G1\text{-}S} = V_{DS} = 0$; $V_{G2\text{-}S}$ = 5 V	–	–	50	nA

DYNAMIC CHARACTERISTICS

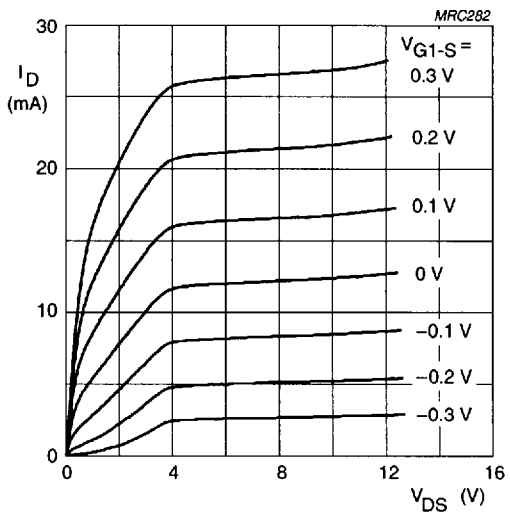
Common source; T_{amb} = 25 °C; V_{DS} = 8 V; $V_{G2\text{-}S}$ = 4 V; I_D = 15 mA; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\lvert y_{fs} \rvert$	forward transfer admittance	pulsed; T_j = 25 °C	36	43	50	mS
$C_{ig1\text{-}s}$	input capacitance at gate 1	f = 1 MHz	2.4	3.1	4	pF
$C_{ig2\text{-}s}$	input capacitance at gate 2	f = 1 MHz	1.2	1.8	2.5	pF
C_{os}	drain-source capacitance	f = 1 MHz	1.2	1.7	2.2	pF
C_{rs}	reverse transfer capacitance	f = 1 MHz	20	30	45	fF
F	noise figure	f = 200 MHz; G_S = 2 mS; $B_S = B_{Sopt}$	–	0.6	1.2	dB
		f = 800 MHz; $G_S = G_{Sopt}$; $B_S = B_{Sopt}$	–	1.5	2.5	dB



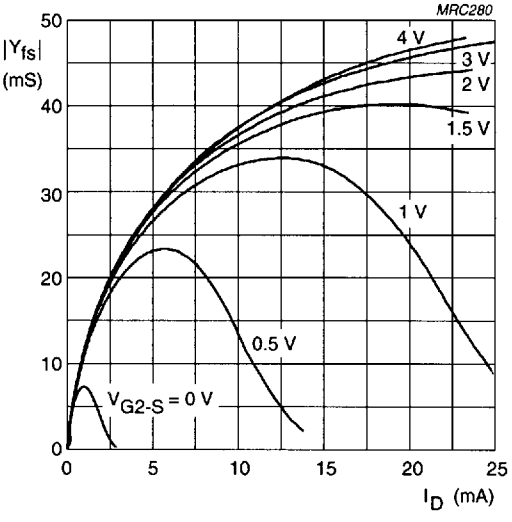
V_{DS} = 8 V.
T_j = 25 °C.

Fig.3 Transfer characteristics; typical values.



V_{G2-S} = 4 V.
T_j = 25 °C.

Fig.4 Output characteristics; typical values.



V_{DS} = 8 V.
T_j = 25 °C.

Fig.5 Forward transfer admittance as a function of drain current; typical values.

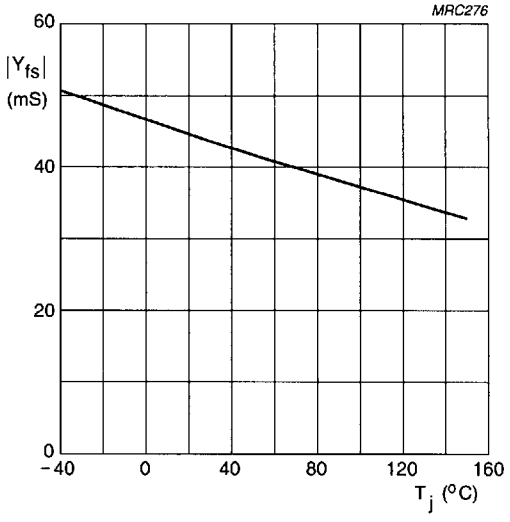
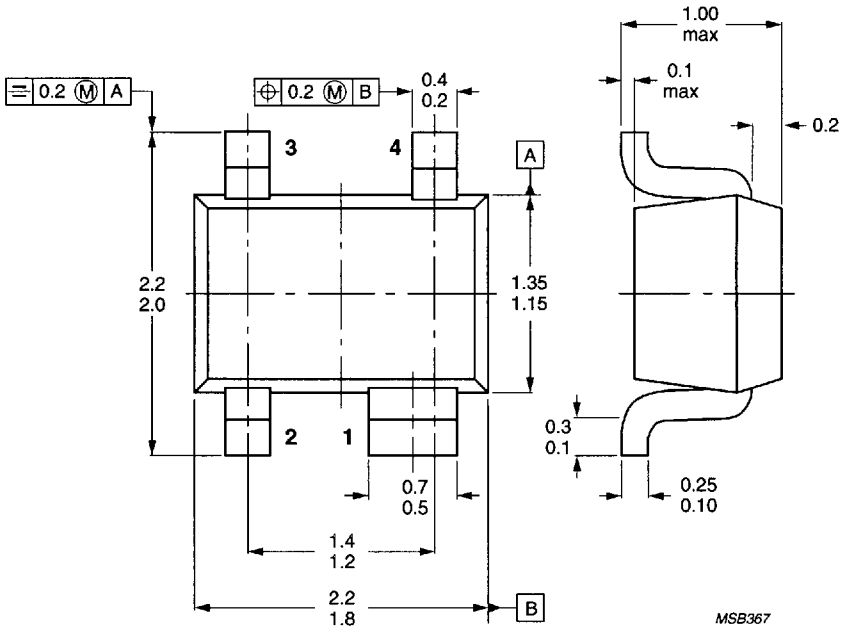


Fig.6 Forward transfer admittance as a function of junction temperature; typical values.

PACKAGE OUTLINE



Dimensions in mm.

Fig.7 SOT343R.